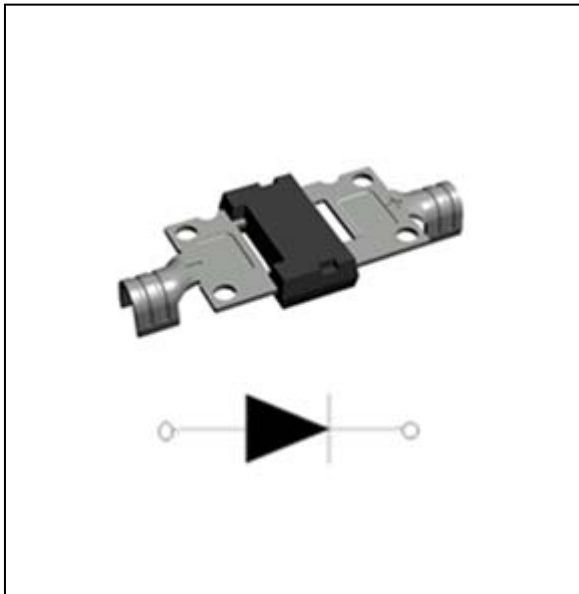




GFMK3045P

Schottky Bypass Diode Module



Features

- High frequency operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability

Typical Applications

Photovoltaic solar cell protection schottky rectifier

Mechanical Data

- **Package:** GF025
Molding compound meets UL 94 V-0 flammability rating,
- **Terminals:** Tin plated leads, solderable per J-STD-002 and JESD 22-B102
- **Polarity:** As marked

■Maximum Ratings ($T_a=25^\circ\text{C}$ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	GFMK3045P
Device marking code			GFMK3045P
Repetitive Peak Reverse Voltage	VRRM	V	45
Average Rectified Output Current @60Hz sine wave, R-load, $T_a=25^\circ\text{C}$	I _O	A	30
Surge(Non-repetitive)Forward Current @60Hz sine wave, 1 cycle, $T_j=25^\circ\text{C}$	I _{FSM}	A	350
Current Squared Time @1ms≤t<8.3ms $T_j=25^\circ\text{C}$, Rating of per diode	I ² t	A ² S	505
Storage Temperature	T _{stg}	°C	-55 ~+150
Junction Temperature IN DC Forward Mode-Forward Operations, without reverse bias, t ≤1 h (Fig. 1) (1)	T _j	°C	-55 ~+200

Note

(1) Meets the requirements of IEC 61215 Ed. 2 bypass diode thermal test.

■Electrical Characteristics ($T_a=25^\circ\text{C}$ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	GFMK3045P
Maximum instantaneous forward voltage drop per diode	V _F	V	I _{FM} =30A	0.55
Maximum DC reverse current at rated DC blocking voltage per diode	I _{RRM}	μA	V _{RM} =V _{RRM}	200

■Thermal Characteristics ($T_a=25^\circ\text{C}$ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	GFMK3045P
Thermal Resistance (1)	R _{θJ-C}	°C/W	1.5

Note

(1) Thermal resistance from Between junction and case, On glass-epoxi substrate.



GFMK3045P

Ordering Information (Example)

PREFERRED P/N	UNIT WEIGHT(g)	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
GFMK3045P	Approximate 4.0	30	600	2400	Tube

Characteristics (Typical)

FIG1:Io -Tc Curve

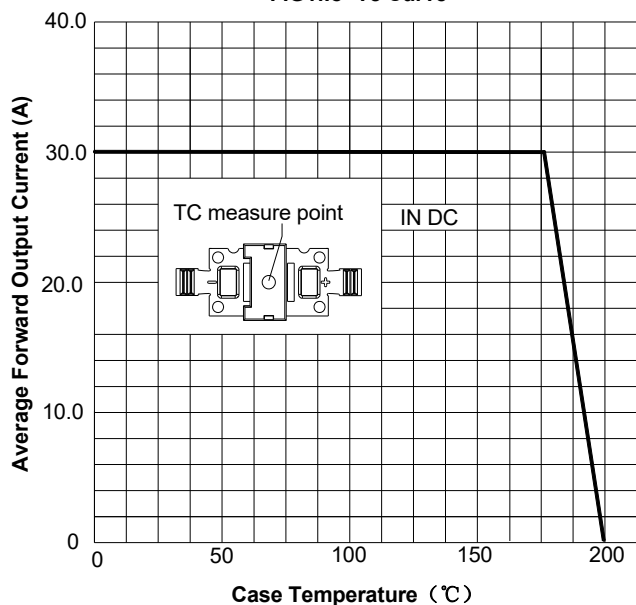


FIG2:Surge Forward Current Capability

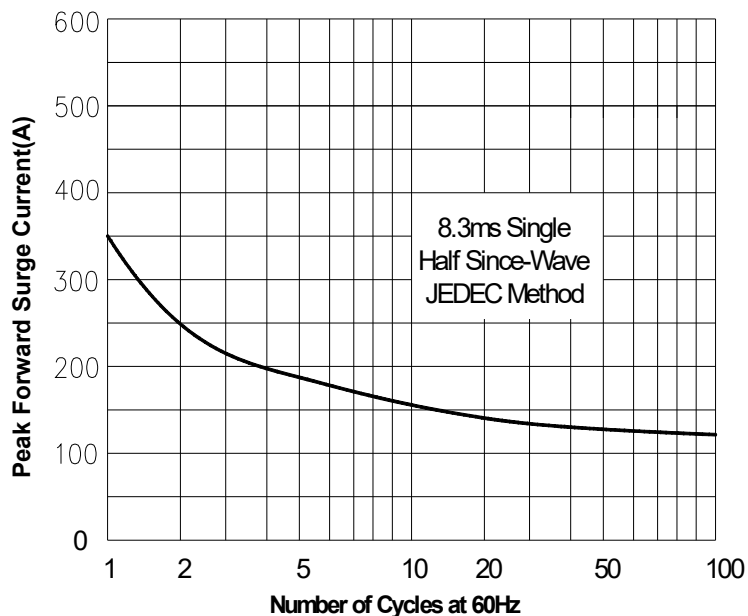


FIG3:Instantaneous Forward Voltage

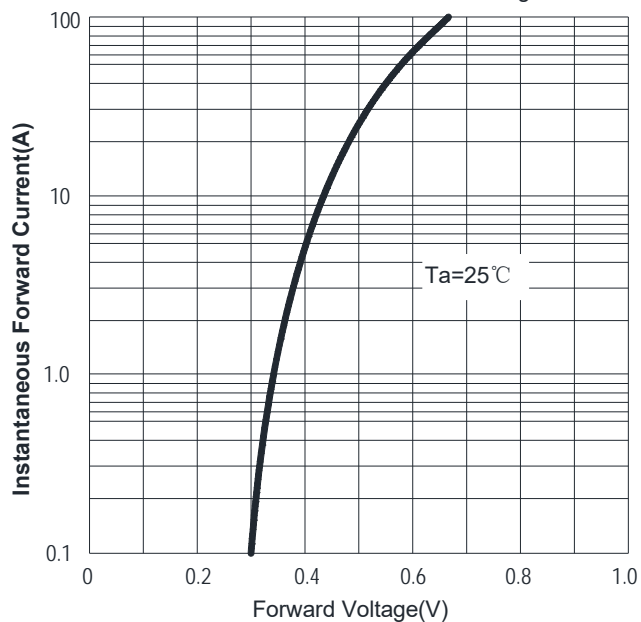
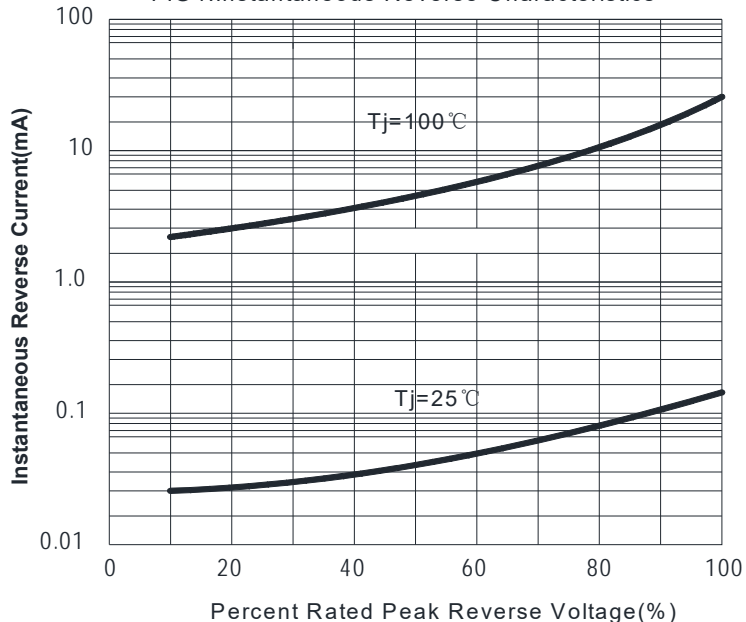
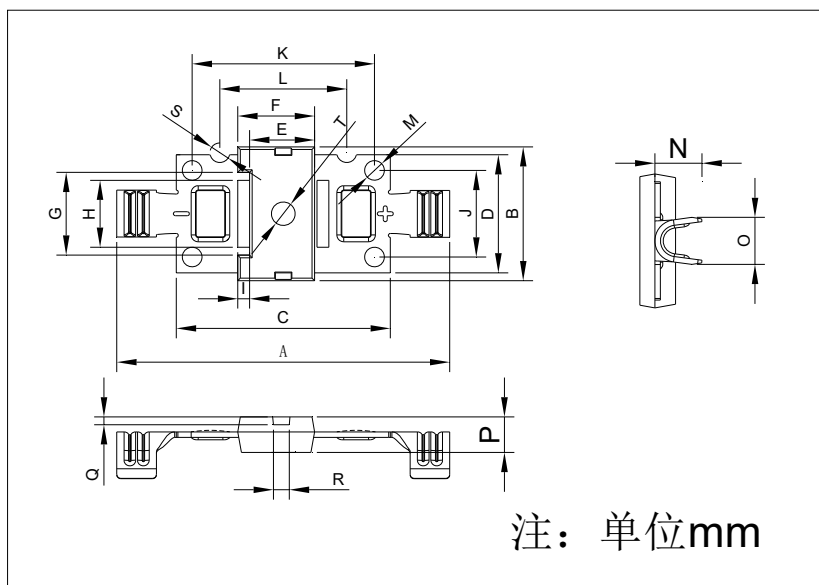


FIG4:Instantaneous Reverse Characteristics



■Outline Dimensions (in millimeters)



DIM	MM		NOTE
	MIN	MAX	
A	41.5	42.5	
B	16.5	17.5	
C	26.5	27.5	
D	14.5	15.5	
E	7.9	8.5	
F	9.4	10	
G	10.50REF		
H	8.2	8.8	
I	1.2	1.8	
J	10.7	11.3	
K	22.7	23.3	
L	15.7	16.3	
M	Φ2.35	Φ2.65	
N	5.65	6.25	
O	5.72	6.22	
P	4.4	4.6	
Q	0.7	1.3	
R	1.7	2.3	
S	Φ2.3	Φ2.7	
T	Φ2.7	Φ3.3	



GFMK3045P

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